



100.00 145 CJC

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the patent of:

KONNO et al.

Patent Number: 5,397,432

Issued: March 14, 1995

For: METHOD FOR PRODUCING SEMICONDUCTOR INTEGRATED CIRCUITS AND APPARATUS USED IN SUCH METHOD

**REQUEST FOR CERTIFICATE OF CORRECTION**

Assistant Commissioner  
for Patents

Washington, D.C. 20231

March 10, 1997

Sir:

The undersigned requests that a Certificate of Correction be issued for the above-identified patent as indicated on the attached Form PTO-1050.

**REMARKS**

This request is being made in order to correct our typographical error in column 11, line 39 and the omission of symbols in Table-1. In support of the corrections to Table-1, we are enclosing a copy of page 24 of the specification.

It is respectfully submitted that no new matter has been added.

Enclosed is a check for One Hundred Dollars (\$100.00) to cover any necessary cost for this change. If however, any additional fees are due, please charge our Deposit Account No. 14-1060.

Respectfully submitted,

NIKAIDO, MARMELSTEIN, MURRAY & ORAM LLP

George E. Oram, Jr.  
Reg. No. 27,931

Atty. Case No. P698-1333

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Enclosures: PTO Form 1050; Copy of Page 24 of the Specification; Check # 12856

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2 145 100.00 DK

Table 1



Conditions	Amount of residual chlorine μm g/cm <sup>2</sup>	10 <sup>15</sup> atoms/cm <sup>2</sup>	After-corrosion	Symbols shown in Fig. 9
① Etching only	0.92±0.06	16.0±1.0	Large	○
② Downflow ashing using O <sub>2</sub> after ①	0.89±0.06	15.5±1.0	Large	●
③ Downflow ashing using O <sub>2</sub> +CF <sub>4</sub> after ①	0.54±0.03	9.3±0.4	Small	■
④ Downflow ashing using O <sub>2</sub> +H <sub>2</sub> O after ①	0.23±0.03	4.0±0.5	No	◊
⑤ Exposure to H <sub>2</sub> O after ② (30sec)	0.51±0.02	8.7±0.3	Small	▲
⑥ Exposure to H <sub>2</sub> O after ② (90sec)	0.48±0.01	8.1±0.2	Small	▲
⑦ Exposure to H <sub>2</sub> O after ② (180sec)	0.45±0.04	7.6±0.7	Small	▲
⑧ Downflow treatment using H <sub>2</sub> O after ② (30sec)	0.28±0.01	4.7±0.2	None	△
⑨ Downflow treatment using H <sub>2</sub> O after ② (90sec)	0.15±0.00	2.5±0.0	No	△
⑩ Downflow treatment using H <sub>2</sub> O after ② (180sec)	0.11±0.01	1.9±0.1	No	△
⑪ Downflow treatment using H <sub>2</sub> after ② (30sec)	0.68±0.01	11.8±0.2	Small	▼
⑫ Downflow treatment using H <sub>2</sub> O after ② (90sec)	0.68±0.01	11.7±0.1	Small	▼
⑬ Downflow treatment using H <sub>2</sub> after ② (180sec)	0.64±0.01	11.1±0.2	Small	▼

Exposure to H<sub>2</sub>O: heated at 120°C in water vapor at 0.1 Torr.

UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION

PATENT NO. : 5,397,432

DATED : March 14, 1995

INVENTOR(S) : KONNO et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby  
corrected as shown below:

Column 11, line 39, delete "or" insert therefor -- and -- *A*

5,397,432

MAILING ADDRESS OF SENDER:

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Suite 330-G Street Lobby  
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Table - 1 insert symbols

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FORM PTO 1050: REV. 1/94

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~~Form PTO-1050 (Rev. 2-27-92)~~

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